



Product data sheet

# 1. Product profile

#### 1.1 General description

High-voltage, high-speed planar-passivated NPN power switching transistor in a SOT78 (TO-220AB) plastic package.

#### **1.2 Features and benefits**

- Fast switching
- High voltage capability

#### **1.3 Applications**

- DC-to-DC converters
- High-frequency electronic lighting ballast applications
- Low thermal resistance
- Inverters
- Motor control systems

#### **1.4 Quick reference data**

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>C</sub>	collector current	see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 4</u>	-	-	4	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; see <u>Figure 3</u>	-	-	80	W
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	-	1050	V
Static cha	racteristics					
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 0.1 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 11</u>	<u>[1]</u> 48	66	100	
		$I_C = 0.8 \text{ A}; V_{CE} = 3 \text{ V};$ $T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 12}{\text{Figure } 12}$	[1] 25	42	50	
		$\frac{1}{100} = 20^{\circ} 0^{\circ}, 000 \frac{1}{100} \frac{1}{12}$				

[1] Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  2 %



## 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		
2	С	collector	mb	С
3	Е	emitter	۲ O ۲	в
mb	С	mounting base; connected to collector		E sym123

SOT78 (TO-220AB)

# 3. Ordering information

#### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUJ302A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

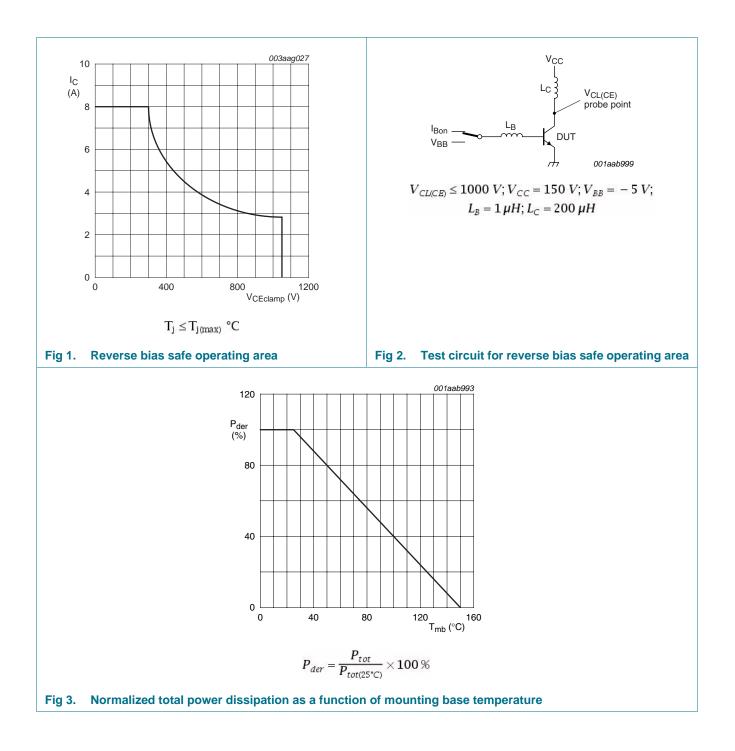
## 4. Limiting values

#### Table 4.Limiting values

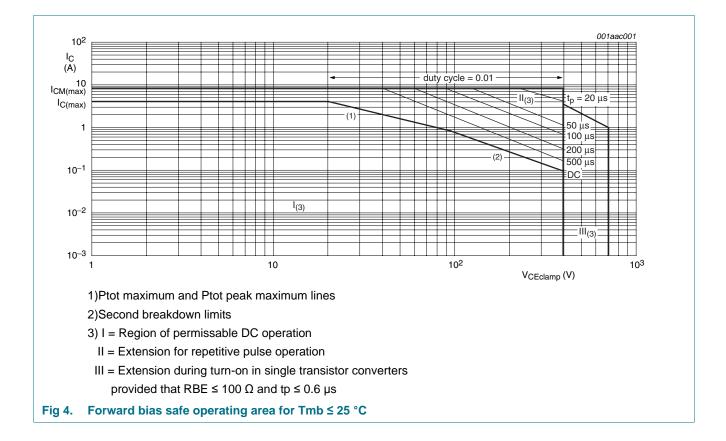
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	1050	V
V <sub>CEO</sub>	collector-emitter voltage	$I_B = 0 A$	-	400	V
I <sub>C</sub>	collector current	see Figure 1; see Figure 2; see Figure 4	-	4	А
I <sub>CM</sub>	peak collector current		-	8	А
I <sub>B</sub>	base current		-	2	А
I <sub>BM</sub>	peak base current		-	4	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; see <u>Figure 3</u>	-	80	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C
V <sub>EBO</sub>	emitter-base voltage	$I_{C} = 0 \text{ A}; I_{E} = 2 \text{ A}; t_{p} < 10 \text{ ms}$	-	24	V

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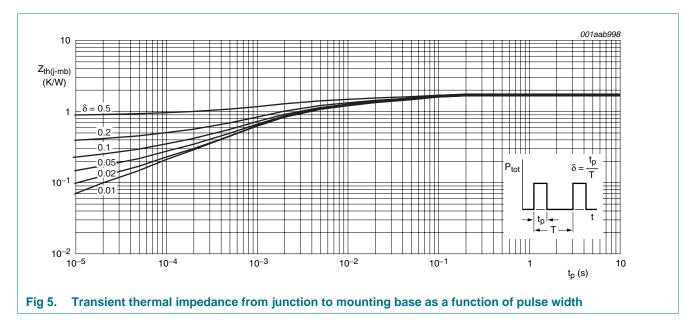




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# 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 5	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W



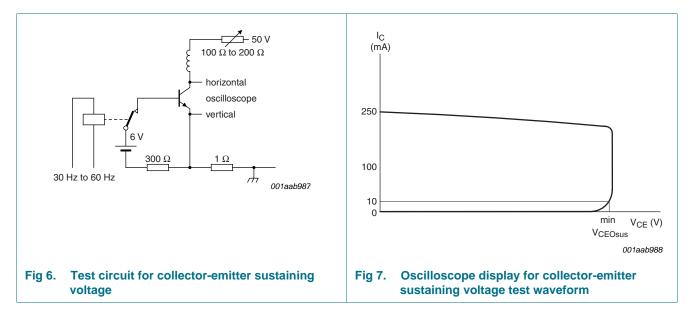
#### Table 5. Thermal characteristics

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# 6. Characteristics

Table 6.	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	aracteristics						
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>BE</sub> = 0 V; V <sub>CE</sub> = 1050 V; T <sub>mb</sub> = 25 °C		-	0.2	10	μΑ
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE}$ = 400 V; I <sub>B</sub> = 0 A; T <sub>mb</sub> = 25 °C		-	10	250	mA
V <sub>(BR)EBO</sub>	open-collector emitter-base breakdown voltage	$I_B = 1 \text{ mA}; I_C = 0 \text{ A}; T_{mb} = 25 \text{ °C}$		15	19	-	V
V <sub>CEOsus</sub>	collector-emitter sustaining voltage	$I_B = 0 \text{ A}; I_C = 10 \text{ mA}; L_C = 25 \text{ mH};$ $T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{\text{Figure 7}};$ see $\frac{\text{Figure 7}}{100000000000000000000000000000000000$	[1]	400	470	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 1 \text{ A}; I_B = 0.2 \text{ A}; T_{mb} = 25 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	<u>[1]</u>	-	0.15	0.5	V
		$I_C = 3.5 \text{ A}; I_B = 1 \text{ A}; T_{mb} = 25 \text{ °C};$ see <u>Figure 8</u> ; see <u>Figure 9</u>	<u>[1]</u>	-	0.6	1.5	V
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 3.5 A; $I_B$ = 1 A; $T_{mb}$ = 25 °C; see <u>Figure 10</u>	<u>[1]</u>	-	1.1	1.5	V
h <sub>FE</sub>	DC current gain	$I_C = 0.1 \text{ A}; V_{CE} = 5 \text{ V}; T_{mb} = 25 \text{ °C};$ see Figure 11	<u>[1]</u>	48	66	100	
		$I_{C} = 0.8 \text{ A}; V_{CE} = 3 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 12</u>	<u>[1]</u>	25	42	50	
Dynamic	characteristics						
t <sub>s</sub>	storage time	I <sub>C</sub> = 2.5 A; I <sub>Bon</sub> = 0.5 A;		-	-	3.5	μs
t <sub>f</sub>	fall time	$I_{Boff} = -0.5 \text{ A}; \text{ R}_{L} = 60 \Omega;$ $V_{BB} = -5 \text{ V}; \text{ T}_{mb} = 25 \text{ °C}; \text{ resistive}$ load; $t_p = 300 \mu\text{s}; \text{ see } \frac{\text{Figure } 13}{\text{Figure } 14}$		-	-	500	ns

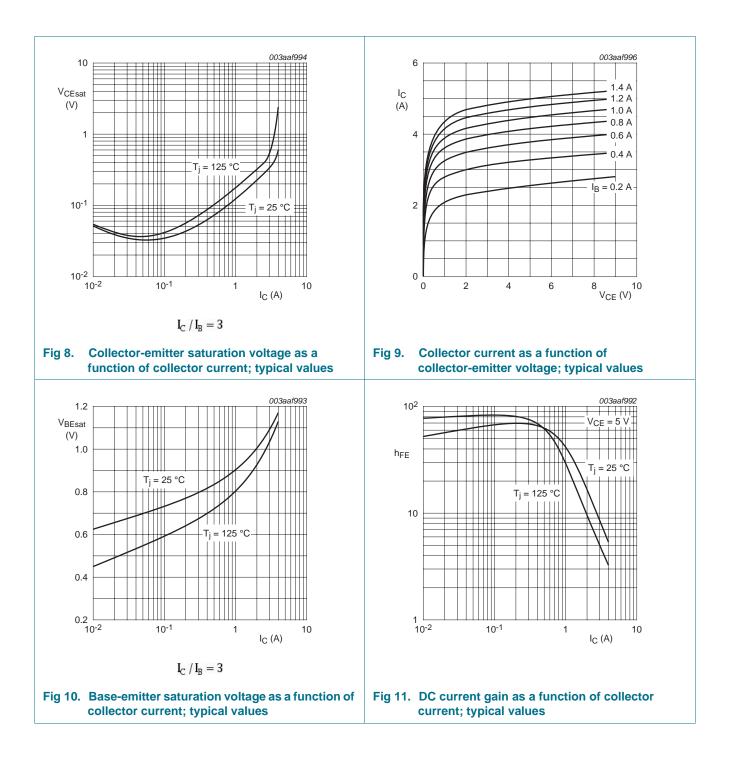
[1] Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  2 %



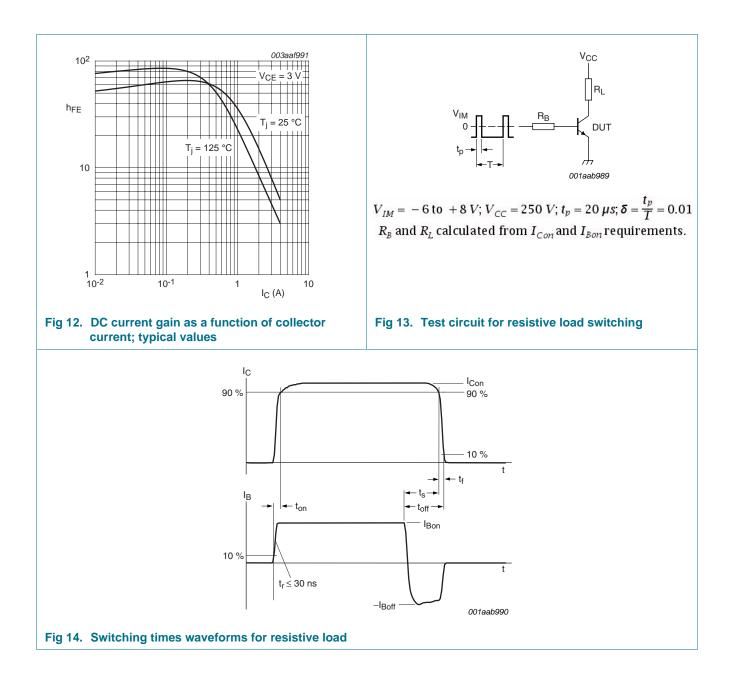
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#### **Package outline** 7.

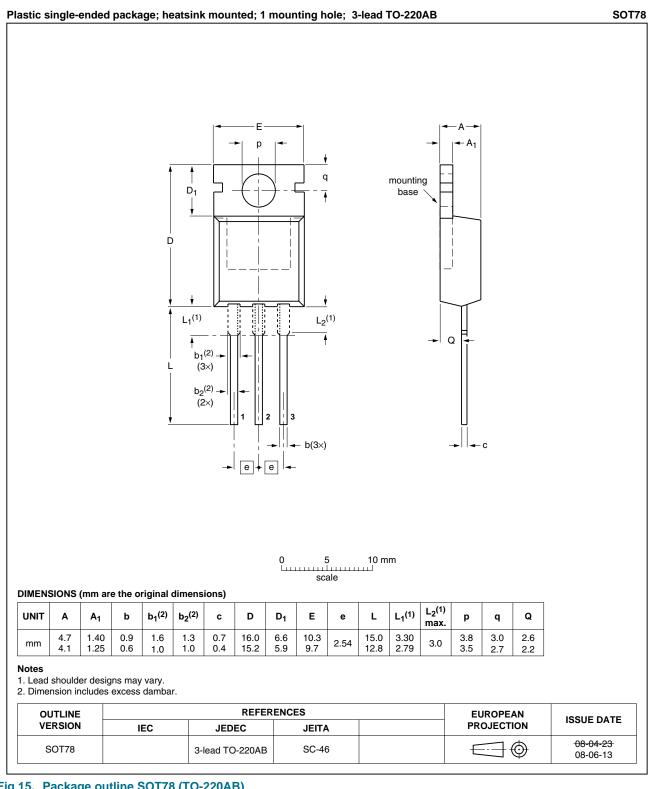


Fig 15. Package outline SOT78 (TO-220AB)

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# 8. Revision history

Table 7. Revisio	on history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUJ302A v.2	20110328	Product data sheet	-	BUJ302A v.1
Modifications:	<ul> <li>The format of of NXP Semic</li> </ul>	this data sheet has been rec onductors.	designed to comply with	the new identity guidelines
	<ul> <li>Legal texts ha</li> </ul>	ve been adapted to the new	company name where	appropriate.
BUJ302A v.1	19980801	Objective specification	n -	-

## 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nxp.com</u>.

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